L Number	Hits	Search Text	DB	Time stamp
1	7243	(electron adj beam) and primary and semiconductor	USPAT;	2004/10/06 15:56
			US-PGPUB;	
			EPO; JPO;	
,			IBM_TDB	
2	628	((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:47
		(circuit adj board)	US-PGPUB;	
			EPO; JPO;	
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3	0	(((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:48
		(circuit adj board)) and (shrinkage near4 board)	US-PGPUB;	
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4	1	(((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:57
		(circuit adj board)) and (shrinkage near4 (board or pattern	US-PGPUB;	
		or circuit))	EPO; JPO; IBM_TDB	*
5	333	(electron adj beam) and (primary adj beam) and	USPAT;	2004/10/06 15:56
	333	semiconductor	US-PGPUB;	2007/10/00 13.30
		Schilediladetoi	EPO; JPO;	
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6	0	((electron adj beam) and (primary adj beam) and	USPAT;	2004/10/06 15:57
		semiconductor) and (shrinkage near4 (board or pattern or	US-PGPUB;	
		circuit))	EPO; JPO;	
		,,,	IBM_TDB	

L Number	Hits	Search Text	DB	Time stamp
1	7243	(electron adj beam) and primary and semiconductor	USPAT; US-PGPUB;	2004/10/06 15:56
			EPO; JPO; IBM_TDB	
2 .	628	((electron adj beam) and primary and semiconductor) and (circuit adj board)	USPAT; US-PGPUB;	2004/10/06 15:47
			EPO; JPO; IBM_TDB	
3.	0	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and (shrinkage near4 board)	USPAT; US-PGPUB;	2004/10/06 15:48
:		(circuit adj boardy) and (similage near board)	EPO; JPO;	
4	1	(((electron adj beam) and primary and semiconductor) and	IBM_TDB USPAT;	2004/10/06 15:57
.		(circuit adj board)) and (shrinkage near4 (board or pattern or circuit))	US-PGPUB; EPO; JPO;	,
5	333	(electron adj beam) and (primary adj beam) and	IBM_TDB USPAT;	2004/10/06 15:56
	333	semiconductor	US-PGPUB;	200-1/10/00 13.30
			EPO; JPO;	,
6	0	((electron adj beam) and (primary adj beam) and	IBM_TDB USPAT;	2004/10/06 15:57
		semiconductor) and (shrinkage near4 (board or pattern or	US-PGPUB;	
		circuit))	EPO; JPO;	
			IBM_TDB	

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1	7243	(electron adj beam) and primary and semiconductor	USPAT;	2004/10/06 15:56
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
2	628	((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:47
		(Circuit adj board)	US-PGPUB;	
	*		EPO; JPO;	
			IBM_TDB	2004/40/06 45.40
3	0	(((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:48
i		(circuit adj board)) and (shrinkage near4 board)	US-PGPUB;	
			EPO; JPO; IBM_TDB	
4	1	(((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:59
"	*	((circuit adj board)) and (shrinkage near4 (board or pattern	US-PGPUB;	200 17 10/00 13.33
		or circuit))	EPO; JPO;	
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5	333	(electron adj beam) and (primary adj beam) and	USPAT;	2004/10/06 15:56
		semiconductor	US-PGPUB;	
			EPO; JPO;	
	(3)		IBM_TDB	
6	0	((electron adj beam) and (primary adj beam) and	USPAT;	2004/10/06 15:57
		semiconductor) and (shrinkage near4 (board or pattern or	US-PGPUB;	
		circuit))	EPO; JPO;	
			IBM_TDB	
7	2	(((==================================	USPAT;	2004/10/06 16:01
		(circuit adj board)) and ((shrinkage or worp\$3) near5 (board	US-PGPUB;	
,		or pattern or circuit))	EPO; JPO;	
			IBM_TDB	

L Number	Hits	Search Text	DB	Time stamp
1	7243	(electron adj beam) and primary and semiconductor	USPAT;	2004/10/06 15:56
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
2	628	((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:47
		(circuit adj board)	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
3	0	(((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:48
		(circuit adj board)) and (shrinkage near4 board)	US-PGPUB;	
			EPO; JPO;	
	a i		IBM_TDB	
4	1	(((electron adj beam) and primary and semiconductor) and	USPAT;	2004/10/06 15:59
		(circuit adj board)) and (shrinkage near4 (board or pattern	US-PGPUB;	
		or circuit))	EPO; JPO;	
_			IBM_TDB	2004/40/06 45 56
5	333	(electron adj beam) and (primary adj beam) and	USPAT;	2004/10/06 15:56
1		semiconductor	US-PGPUB;	
			EPO; JPO;	
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6	0	((electron adj beam) and (primary adj beam) and	USPAT;	2004/10/06 15:57
		semiconductor) and (shrinkage near4 (board or pattern or	US-PGPUB;	
		circuit))	EPO; JPO;	
-,		(//electron adi beam) and primary and comiconductor) and	IBM_TDB USPAT;	2004/10/06 16:01
7	2	(((electron adj beam) and primary and semiconductor) and	US-PGPUB;	2007/10/00 10.01
		(circuit adj board)) and ((shrinkage or worp\$3) near5 (board	EPO; JPO;	
		or pattern or circuit))	IBM_TDB	
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